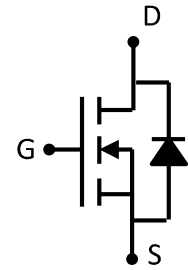


Feature

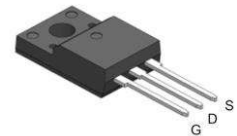
- 200V,18A
 $R_{DS(ON)} < 170m\Omega @ V_{GS}=10V$ TYP:130 m Ω
- Advanced Planar stripe DMOS Technology
- Lead free product is acquired
- Excellent $R_{DS(ON)}$ and Low Gate Charge



Schematic diagram

Application

- PWM applications
- Load Switch
- Power management



TO-220F

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity (PCS)
18N20	AP18N20FL	TO-220F	-	-	50

ABSOLUTE MAXIMUM RATINGS ($T_a=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	200	V
Gate-Source Voltage	V_{GS}	± 30	V
Continuous Drain Current ($T_a = 25^\circ\text{C}$)	I_D	18	A
Continuous Drain Current ($T_a = 100^\circ\text{C}$)	I_D	9	A
Pulsed Drain Current ⁽¹⁾	I_{DM}	72	A
Singel Pulsed Avalanche Energy ⁽²⁾	E_{AS}	450	mJ
Power Dissipation	P_D	35	W
Thermal Resistance from Junction to Case	$R_{\theta JC}$	3.57	$^\circ\text{C}/\text{W}$
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature	T_{STG}	-55~ +150	$^\circ\text{C}$

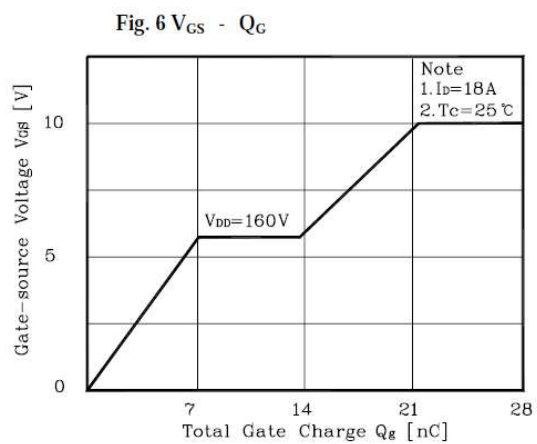
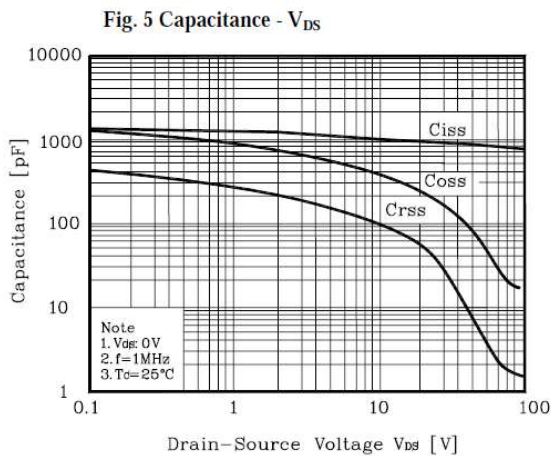
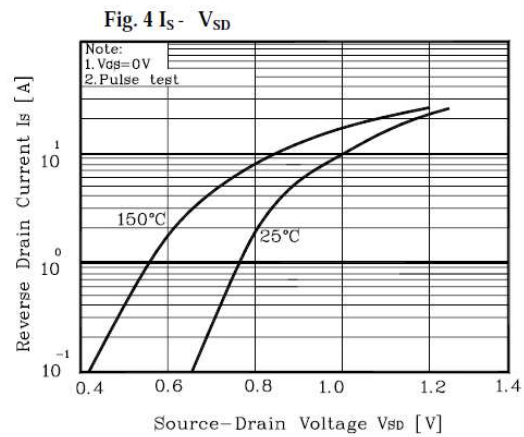
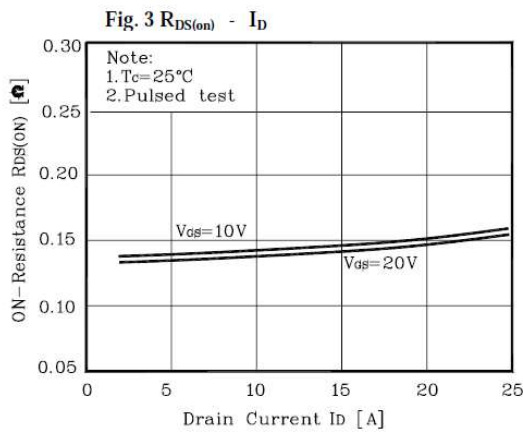
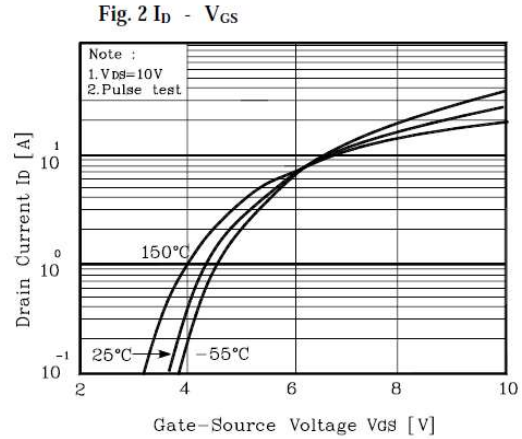
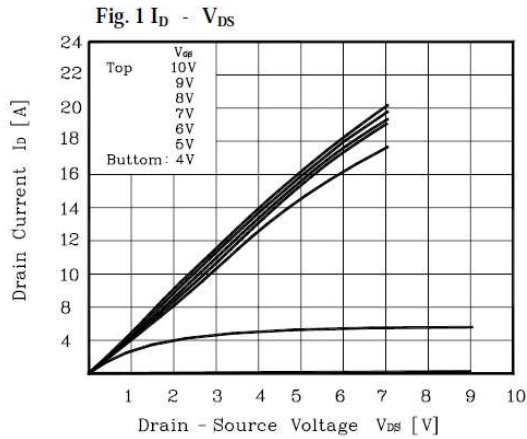
MOSFET ELECTRICAL CHARACTERISTICS($T_a=25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Type	Max	Unit
Static Characteristics						
Drain-source breakdown voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	200	-	-	V
Zero gate voltage drain current	I_{DSS}	$V_{DS} = 200V, V_{GS} = 0V$	-	-	1	μA
Gate-body leakage current	I_{GSS}	$V_{GS} = \pm 30V, V_{DS} = 0V$	-	-	± 100	nA
Gate threshold voltage ⁽³⁾	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	1	1.8	2.5	V
Drain-source on-resistance ⁽³⁾	$R_{DS(on)}$	$V_{GS} = 10V, I_D = 9A$	-	130	170	m Ω
Forward tranconductance ⁽³⁾	g_{FS}	$V_{DS} = 10V, I_D = 9A$	-	10.5	-	S
Dynamic characteristics						
Input Capacitance	C_{iss}	$V_{DS} = 25V, V_{GS} = 0V, f = 100kHz$	-	940	-	pF
Output Capacitance	C_{oss}		-	225	-	
Reverse Transfer Capacitance	C_{rss}		-	55	-	
Switching characteristics						
Turn-on delay time	$t_{d(on)}$	$V_{DD} = 125V, I_D = 18A, V_{GS} = 10V,$ $R_G = 25\Omega$	-	15	-	ns
Turn-on rise time	t_r		-	130	-	
Turn-off delay time	$t_{d(off)}$		-	135	-	
Turn-off fall time	t_f		-	105	-	
Total Gate Charge	Q_g	$V_{DS} = 160V, I_D = 18A,$ $V_{GS} = 10V$	-	22	-	nC
Gate-Source Charge	Q_{gs}		-	6.6	-	
Gate-Drain Charge	Q_{gd}		-	7.2	-	
Source-Drain Diode characteristics						
Diode Forward voltage ⁽³⁾	V_{DS}	$V_{GS} = 0V, I_S = 9A$	-	-	1.4	V
Diode Forward current ⁽⁴⁾	I_S		-	-	18	A
Body Diode Reverse Recovery Time	t_{rr}	$T_J = 25^{\circ}, I_F = 18A, di/dt = 100A/\mu s$		207		ns
Body Diode Reverse Recovery Charge	Q_{rr}	$T_J = 25^{\circ}, I_F = 18A, di/dt = 100A/\mu s$		1.63		uc

Notes:

1. Repetitive Rating: pulse width limited by maximum junction temperature
2. EAS Condition: $T_J = 25^{\circ}\text{C}, V_{DD} = 50V, R_G = 50\Omega, L = 0.5\text{mH}$
3. Pulse Test: pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$
4. Surface Mounted on FR4 Board, $t \leq 10\text{ sec}$

Typical Characteristics



Typical Characteristics

Fig. 7 $V_{DS} - T_J$

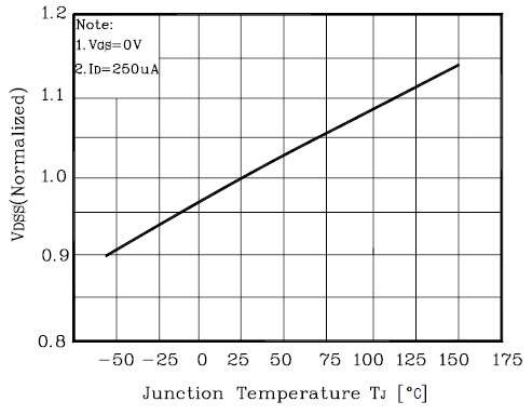


Fig. 8 $R_{DS(on)} - T_J$

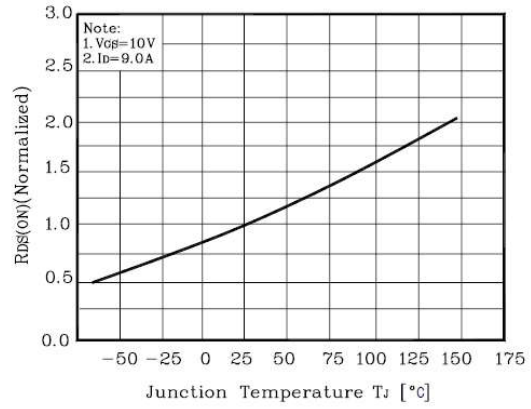


Fig. 9 $I_D - T_C$

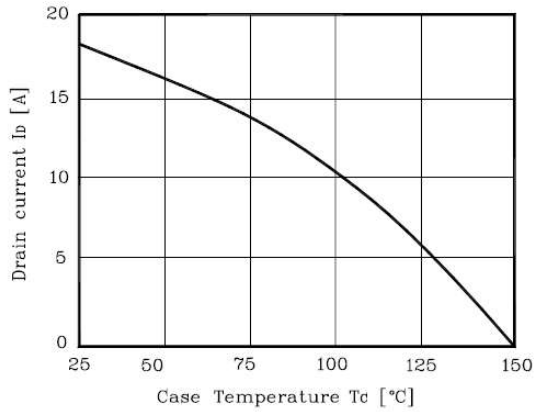


Fig. 10 Safe Operating Area

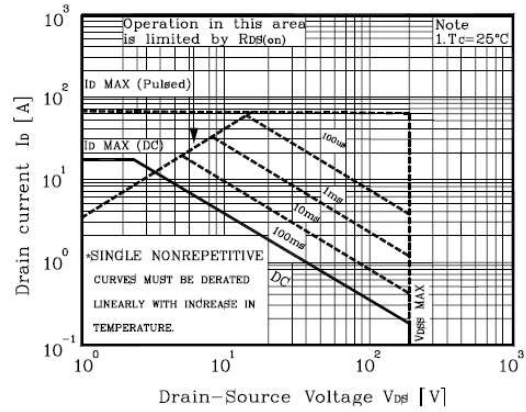


Fig 11. Gate Charge Test Circuit & Waveform

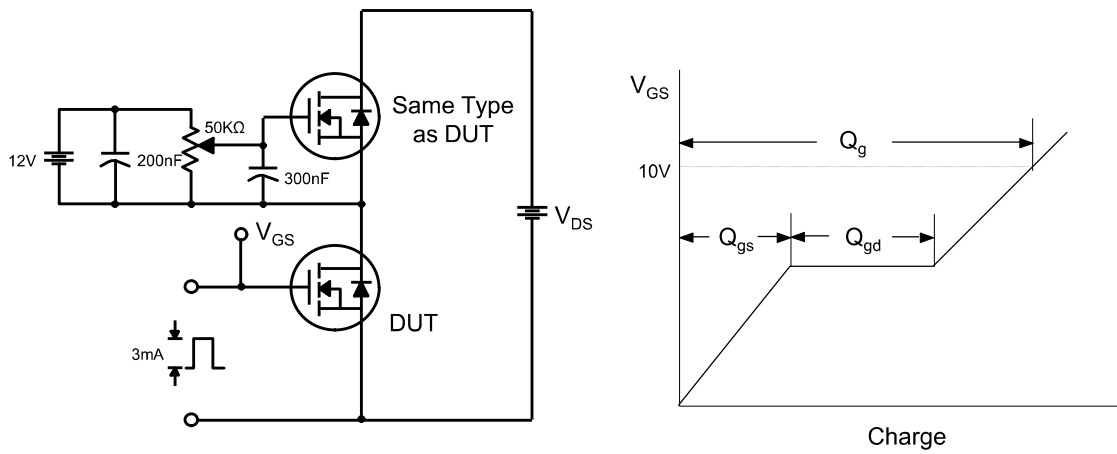


Fig 12. Resistive Switching Test Circuit & Waveforms

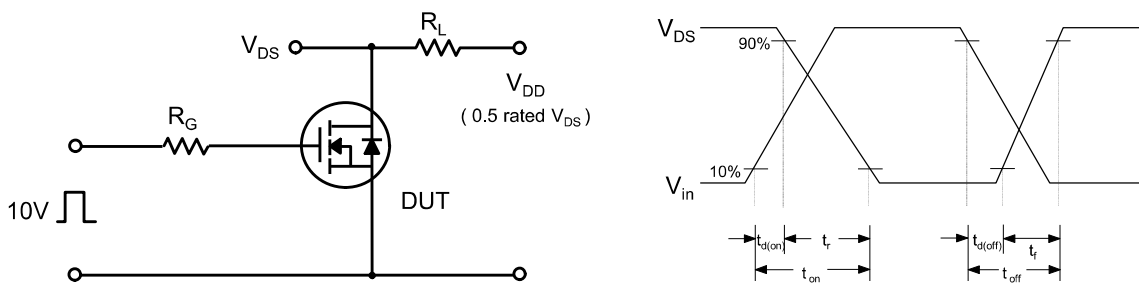


Fig 13. Unclamped Inductive Switching Test Circuit & Waveforms

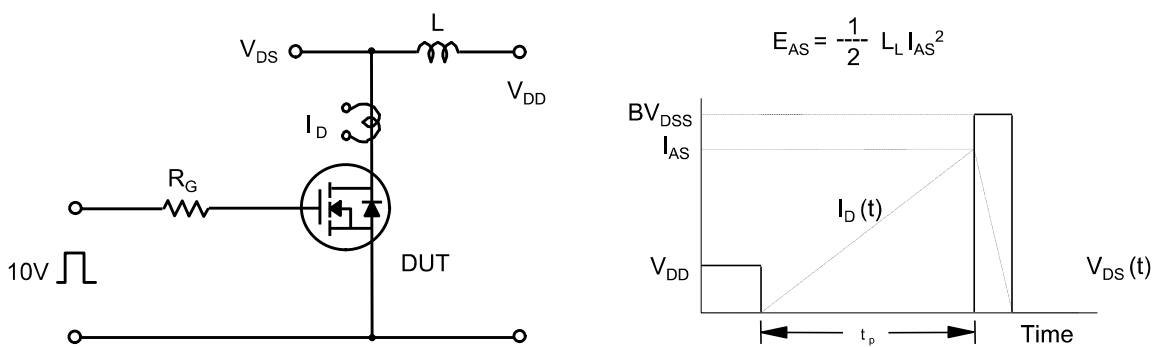
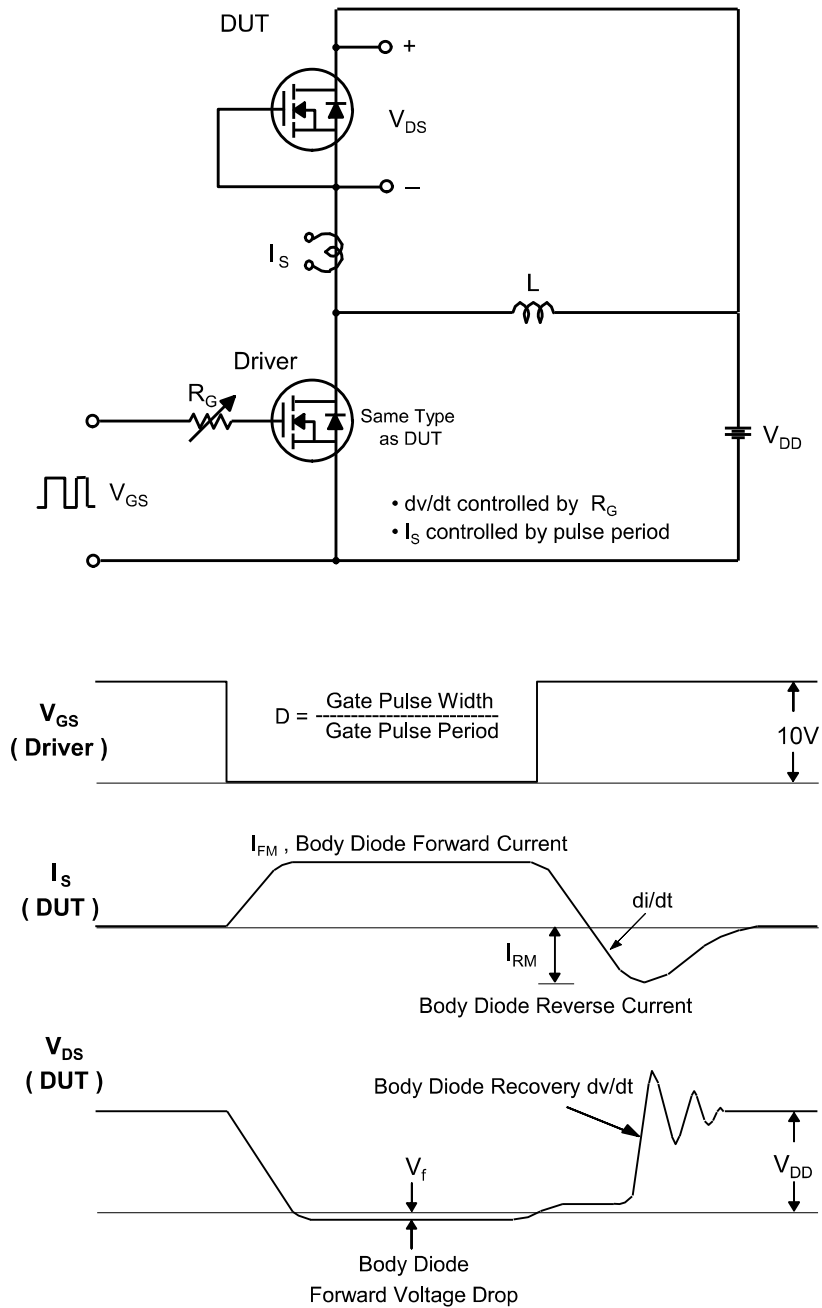
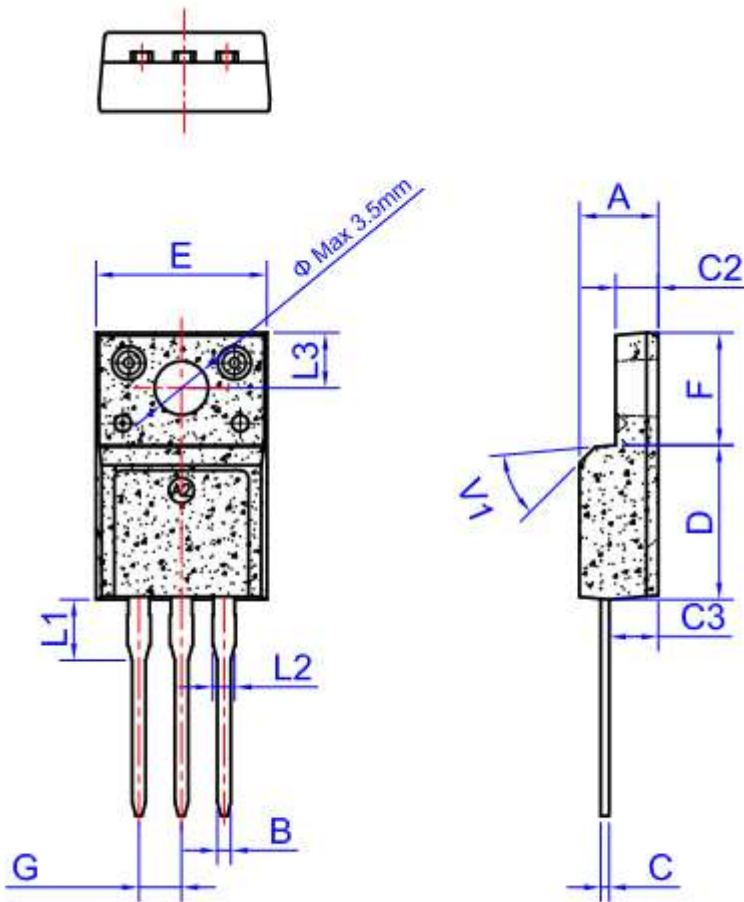


Fig 14. Peak Diode Recovery dv/dt Test Circuit & Waveforms



Package Outlines



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.50		4.90	0.177		0.193
B	0.74	0.80	0.83	0.029	0.031	0.033
C	0.47		0.65	0.019		0.026
C2	2.45		2.75	0.096		0.108
C3	2.60		3.00	0.102		0.118
D	8.80		9.30	0.346		0.366
E	9.80		10.4	0.386		0.410
F	6.40		6.80	0.252		0.268
G		2.54			0.1	
H	28.0		29.8	1.102		1.173
L1		3.63			0.143	
L2	1.14		1.70	0.045		0.067
L3		3.30			0.130	
V1		45°			45°	